

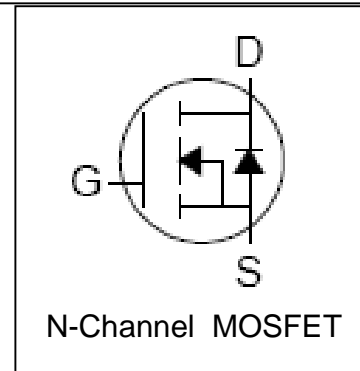
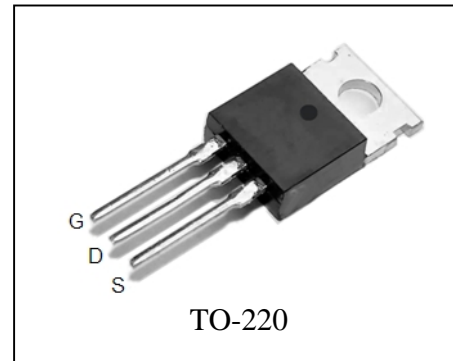
Features

- 75V/80A,
 $R_{DS(ON)} = 8m$ (Typ.) @ $V_{GS} = 10V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- 100% avalanche tested
- Lead Free and Green Devices Available
 (RoHS Compliant)

Applications

- Motor Control

Pin Description



Absolute Maximum Ratings

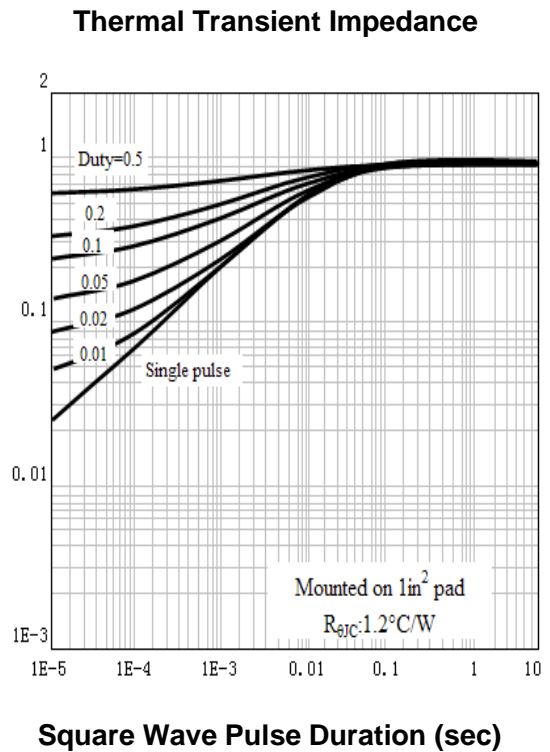
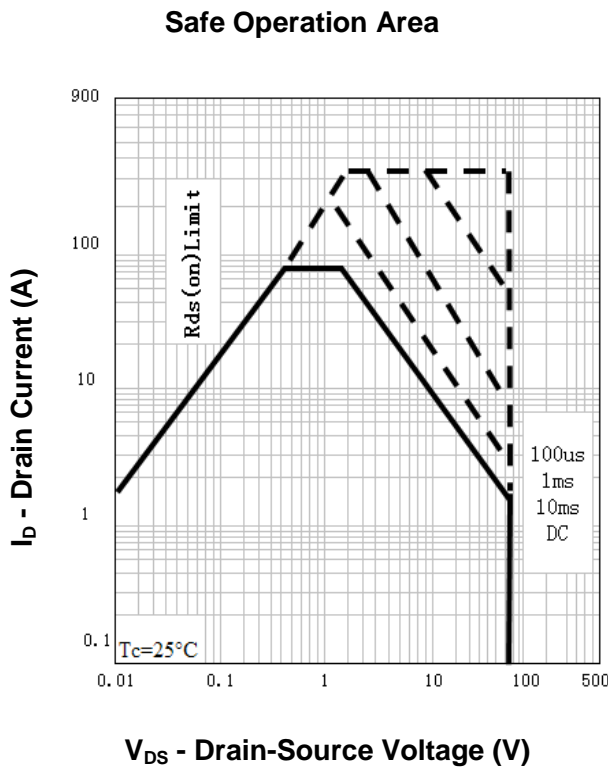
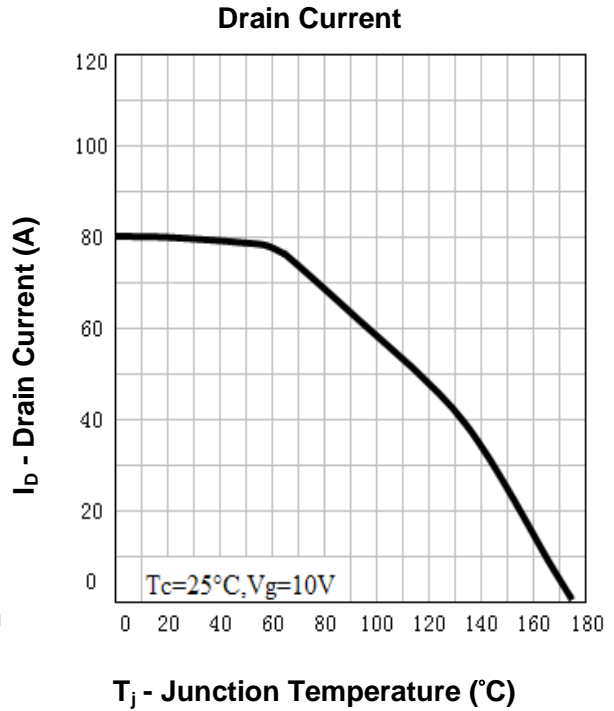
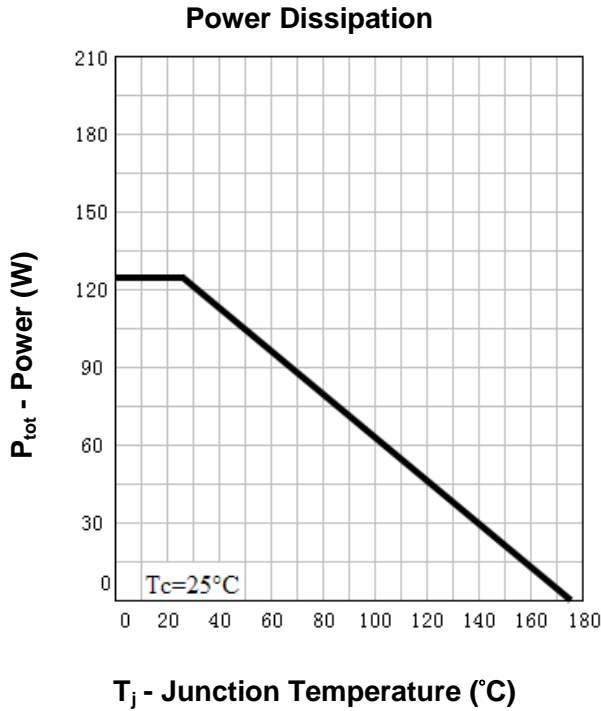
Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	75	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ C$ 80	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C = 25^\circ C$ 320 ^①	A
I_D	Continuous Drain Current ($V_{GS} = 10V$)	$T_C = 25^\circ C$ 80	A
		$T_C = 100^\circ C$ 58	
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$ 125	W
		$T_C = 100^\circ C$ 62.5	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.2	$^\circ C/W$
Drain-Source Avalanche Ratings			
E_{AS} ^②	Avalanche Energy, Single Pulsed	169	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU7580R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	75			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=75V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1	μA
					30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(3)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=40A$		8	10	m Ω
Diode Characteristics						
$V_{SD}^{(3)}$	Diode Forward Voltage	$I_{SD}=20A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=40A, di_{SD}/dt=100A/\mu s$		43		ns
Q_{rr}	Reverse Recovery Charge			90		nC
Dynamic Characteristics ⁽⁴⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.6		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=35V,$ Frequency=1.0MHz		3650		pF
C_{oss}	Output Capacitance			980		
C_{riss}	Reverse Transfer Capacitance			265		
$t_{d(ON)}$	Turn-on Delay Time			41		
t_r	Turn-on Rise Time	$V_{DD}=35V, R_L=0.8\Omega,$ $I_{DS}=40A, V_{GEN}=10V,$ $R_G=4.7\Omega$		135		ns
$t_{d(OFF)}$	Turn-off Delay Time			180		
t_f	Turn-off Fall Time			92		
Gate Charge Characteristics ⁽⁴⁾						
Q_g	Total Gate Charge	$V_{DS}=60V, V_{GS}=10V,$ $I_{DS}=40A$		67		nC
Q_{gs}	Gate-Source Charge			15		
Q_{gd}	Gate-Drain Charge			25		

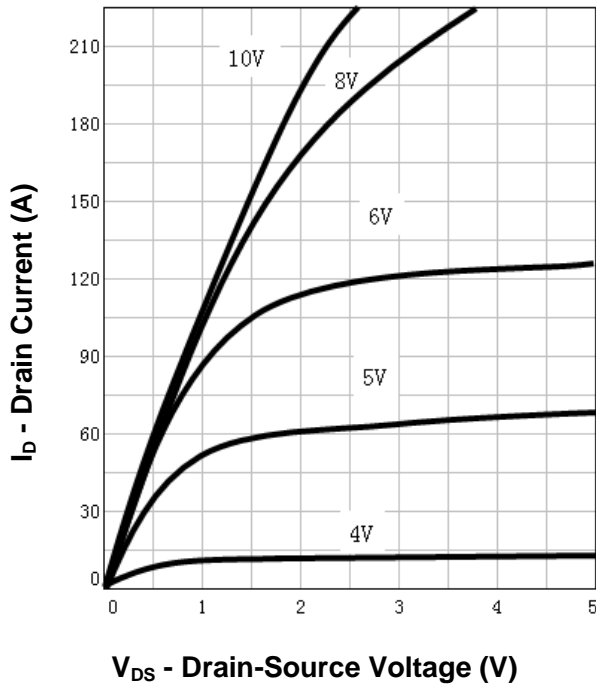
- Notes: ① Pulse width limited by safe operating area.
 ② Limited by T_{Jmax} , $I_{AS}=26A$, $V_{DD}=48V$, $R_G=50\Omega$, Starting $T_J=25^\circ\text{C}$.
 ③ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ④ Guaranteed by design, not subject to production testing.

Typical Characteristics

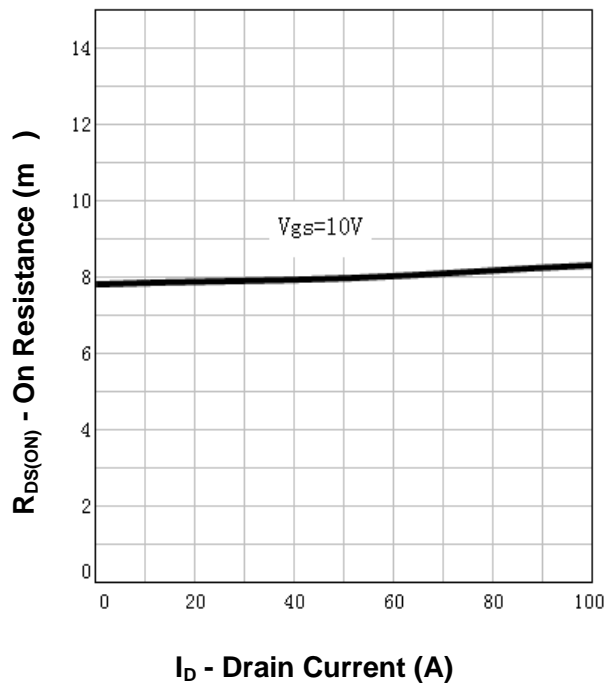


Typical Characteristics

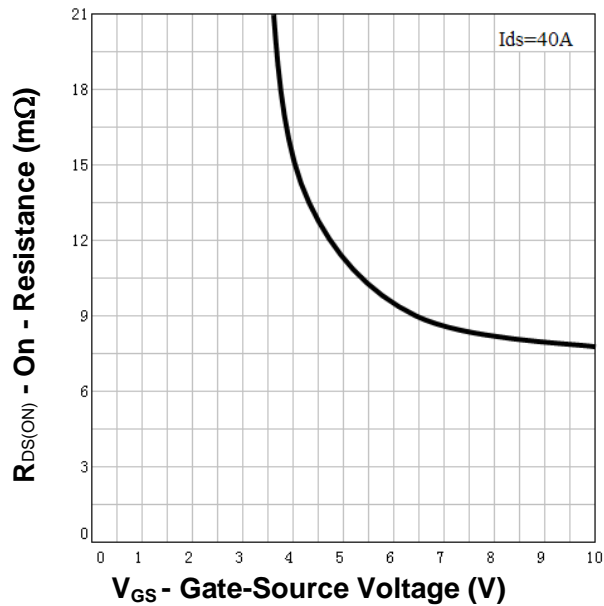
Output Characteristics



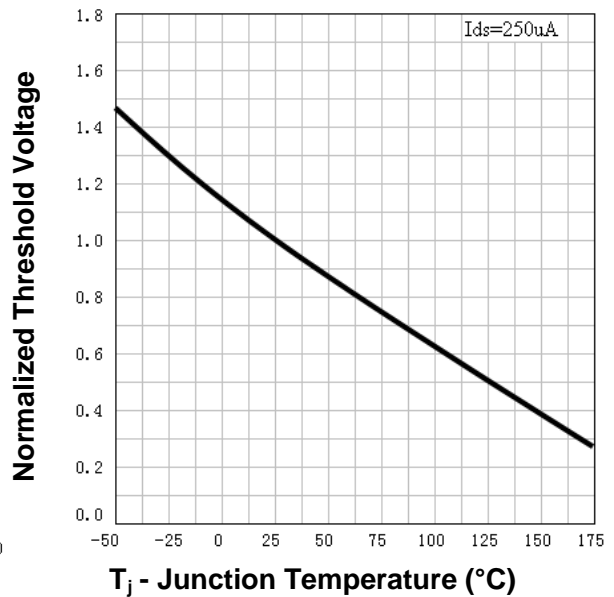
Drain-Source On Resistance



Drain-Source On Resistance

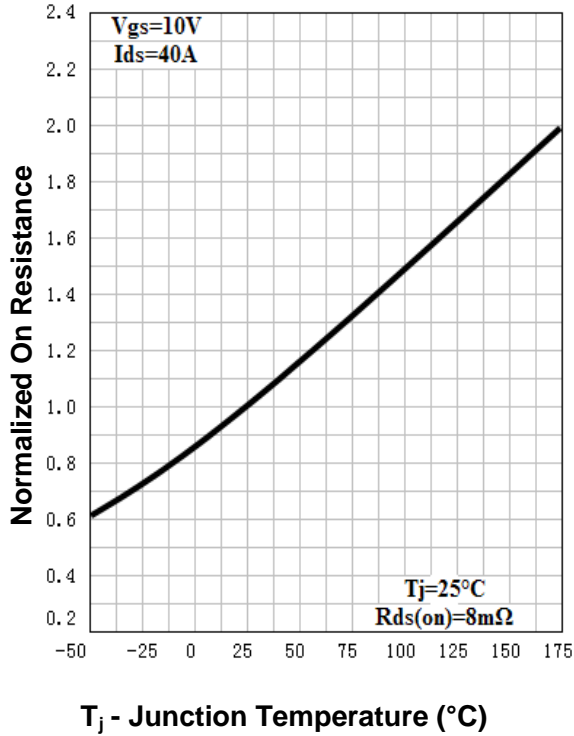


Gate Threshold Voltage

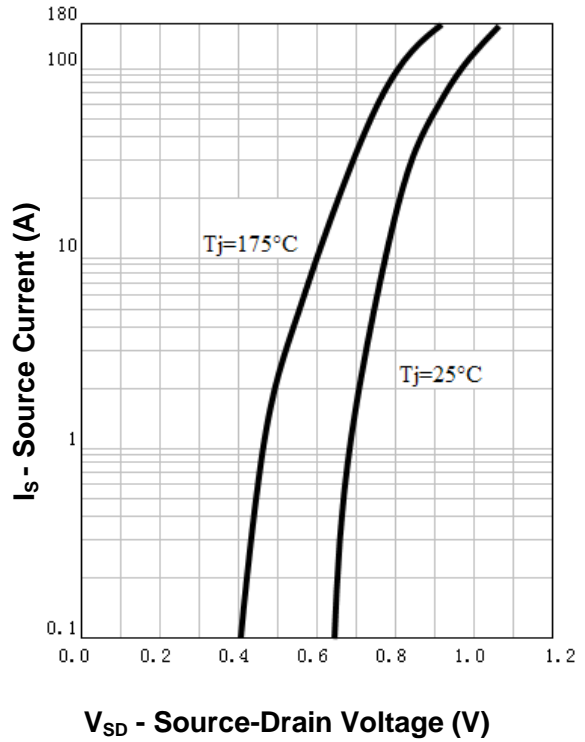


Typical Characteristics

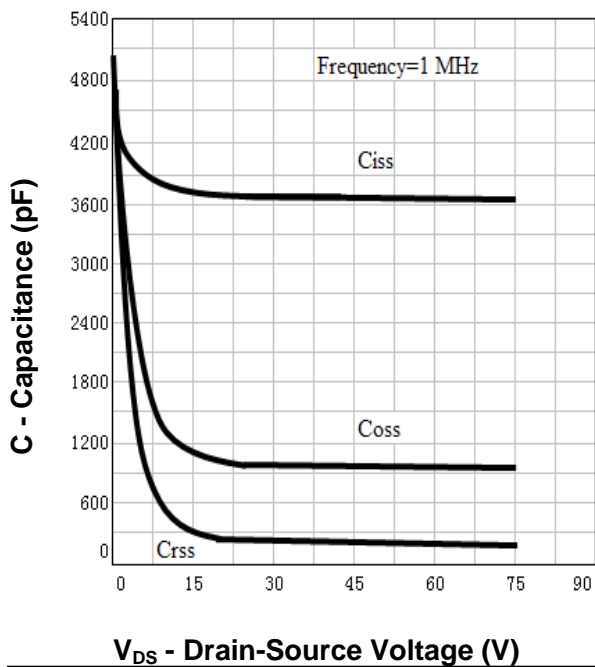
Drain-Source On Resistance



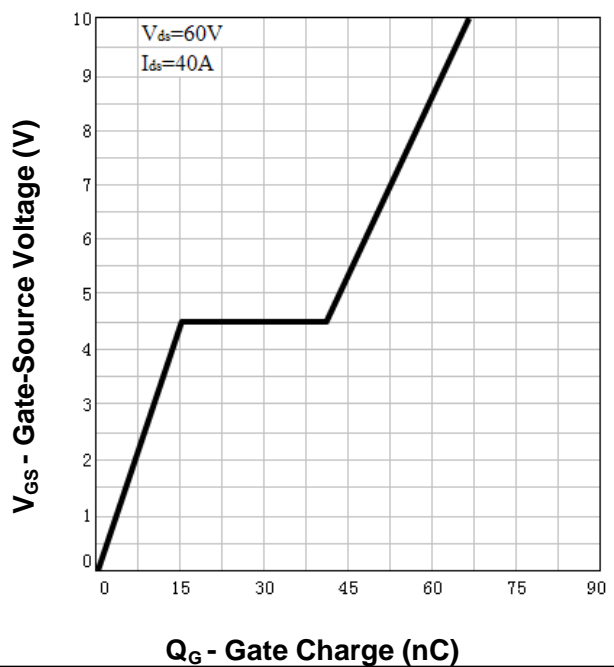
Source-Drain Diode Forward



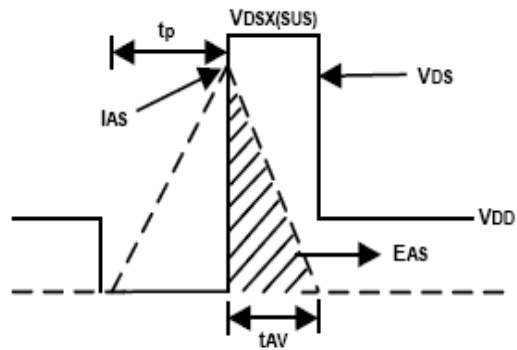
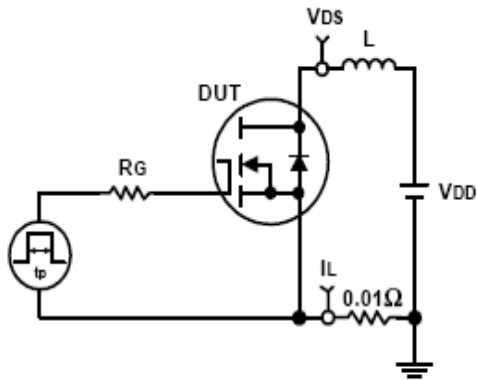
Capacitance



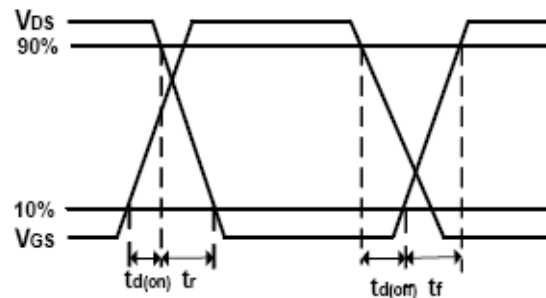
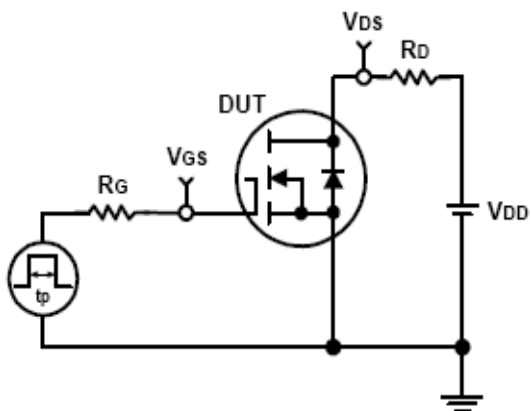
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU7580R	RU7580R	TO-220	Tube	50	-	-

Package Information

TO-220FB-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	ϕp	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	$\theta 1$	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	$\theta 2$	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

Room 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA

TEL: (86-755) 8311-5334

FAX: (86-755) 8311-4278

E-mail: Sales-SZ@ruichips.com